

IN THE SPECIFICATION:

Please amend the specification as follows:

On page 5, please amend the paragraph beginning on line 16 as follows:

Fig. 9 is a plan view illustrating a conventional comb-shape structured transistor as a low-noise transistor which has hitherto been used; ~~and~~

On page 5, please amend the paragraph beginning on line 19 as follows:

Fig. 10 is a sectional view of the device, showing a problem inherent in a prior art input transistor[.]; and

On page 5, please insert the following paragraph after line 20:

Fig. 11 is a plan view illustrating a plurality of MOSFETs disposed in a comb-like shape on the semiconductor substrate to form an amplifier stage in accordance with the present invention.

On page 5, please amend the paragraph beginning on line 26 as follows:

FIG. 1 is a plan view showing a layout of a semiconductor device in a first embodiment of the present invention. FIG. 2A shows a cross sectional view of the semiconductor device along the line a-a' in FIG. 1 and FIG. 2B shows a cross sectional view of the semiconductor device along the line b-b' in FIG. 1. FIGS. 1, 2A and 2B show a gate area of a MOSFET at an input stage of a low-noise amplifier. Fig. 11 shows a plurality of MOSFETs arranged in a comb-like shape to form an amplifier stage. Throughout FIGS. 1, 2A and 2B, the elements corresponding to those in the prior art explained in FIGS. 9 and 10 are marked with the reference numerals 100s.